

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-12. (Canceled)

13. (Currently Amended) A thin-film magnetic head having a magnetoresistive element and a dummy component that are formed on a base, wherein:

the magnetoresistive element ~~being is~~ formed by etching a part of a film for the magnetoresistive element, the film having a specific shape and being used for forming the magnetoresistive element, ~~in its thickness direction in a specific region within the film; and~~ element;

the film for the magnetoresistive element includes a first region and a second region;

the film is not etched in the first region but etched in the second region partway in a direction from its top surface toward the base;

the dummy component ~~being is~~ formed by etching a part of a dummy film ~~in its thickness direction~~ in its entire region partway in a direction from its top surface toward the base, the dummy film having a composition the same as that of the film for the magnetoresistive element and not being used for forming the magnetoresistive ~~element~~ element; and

one of surfaces of the dummy component farther from the base is located at a position corresponding to a position of a surface of the film for the magnetoresistive element in the second region that is obtained by the etching, as viewed in a direction of thickness of the magnetoresistive element.

14. (Original) A thin-film magnetic head according to claim 13, wherein the magnetoresistive element includes a first magnetic layer, a tunnel barrier layer and a second magnetic layer that are stacked in this order on the base.

15. (Currently Amended) A thin-film magnetic head according to claim 14, wherein the one of the surfaces of the dummy component farther from the base is located at a position

corresponding to a boundary between the second magnetic layer and the tunnel barrier layer of the magnetoresistive ~~element~~element, as viewed in a direction of thickness of the magnetoresistive element.

16. (Currently Amended) A thin-film magnetic head according to claim 14, wherein the one of the surfaces of the dummy component farther from the base is located at a position corresponding to a position located partway through the tunnel barrier layer of the magnetoresistive ~~element~~element, as viewed in a direction of thickness of the magnetoresistive element.

17. (Currently Amended) A thin-film magnetic head according to claim 14, wherein the one of the surfaces of the dummy component farther from the base is located at a position corresponding to a boundary between the tunnel barrier layer and the first magnetic layer of the magnetoresistive ~~element~~element, as viewed in a direction of thickness of the magnetoresistive element.

18. (Currently Amended) A thin-film magnetic head according to claim 14, wherein the one of the surfaces of the dummy component farther from the base is located at a position corresponding to a position located partway through the first magnetic layer of the magnetoresistive ~~element~~element, as viewed in a direction of thickness of the magnetoresistive element.

19. (Original) A thin-film magnetic head according to claim 13, further having a metallic layer that serves as the base on which the magnetoresistive element and the dummy component are formed.

20. (Original) A thin-film magnetic head according to claim 19, wherein the metallic layer is formed of a non-magnetic metal.

21. (Original) A thin-film magnetic head according to claim 13, wherein the dummy component is formed at a position where it is hidden from an integrated surface by a patterned thin film formed after the dummy component has been formed.

22. (Original) A thin-film magnetic head according to claim 13, wherein the dummy component has a shape that represents a symbol for identifying each individual thin-film magnetic head.

23. (Original) A thin-film magnetic head according to claim 13, wherein a region in which the dummy component is provided has an area that falls within a range of 0.05 to 30 percent of the area of a surface of the thin-film magnetic head on which the magnetoresistive element and the dummy component are provided.

24. (Original) A thin-film magnetic head according to claim 13, wherein a region in which the dummy component is provided has an area that falls within a range of 0.1 to 20 percent of the area of a surface of the thin-film magnetic head on which the magnetoresistive element and the dummy component are provided.

25. (Canceled)